CM150DX-24A

HIGH POWER SWITCHING USE
INSULATED TYPE

CM150DX-24A **- 5th Generation NX series -**

Dual (Half-Bridge)

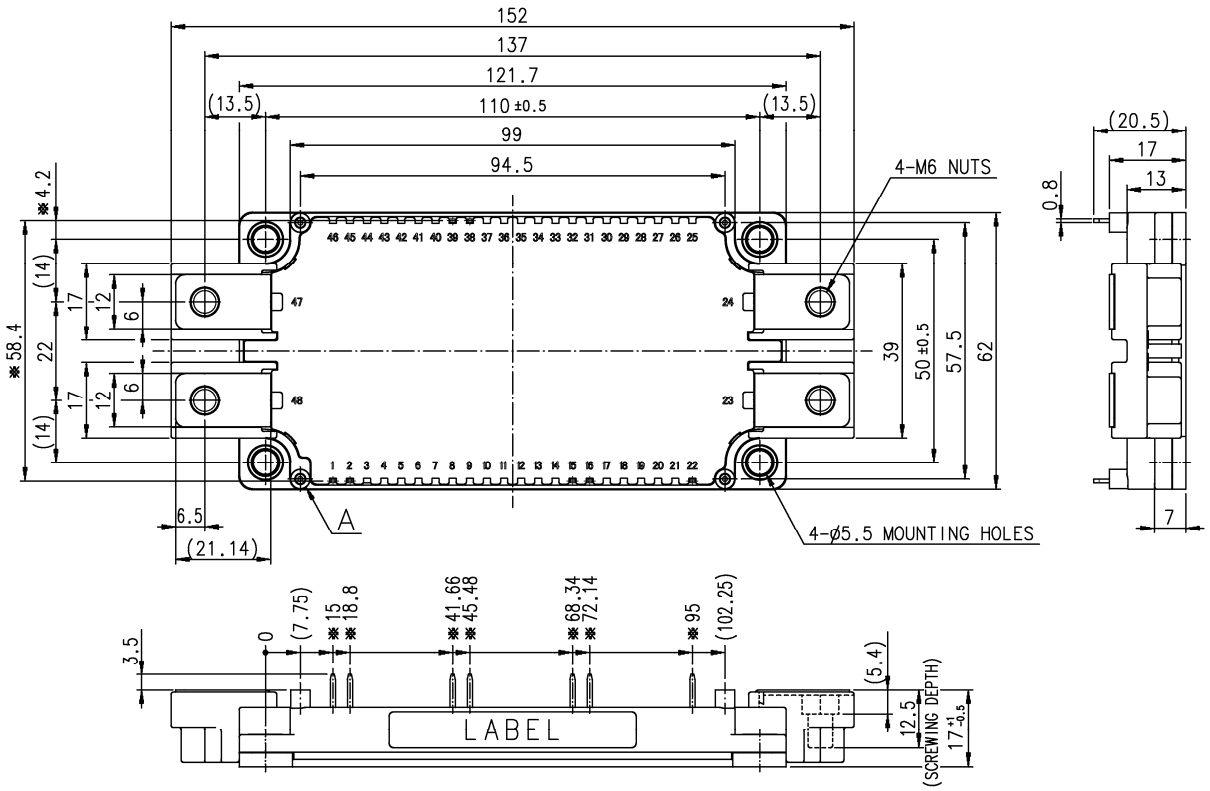
Collector current I_C ..... **150** A
Collector-emitter voltage V_{CES} ..... **1200** V
Maximum junction temperature T_{jmax} ... **150** °C

- ●Flat base Type
- ●Copper base plate (non-plating)
- ●RoHS Directive compliant
- ●UL Recognized under UL1557, File E323585

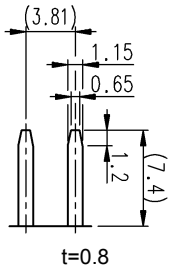
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION **Dimension in mm**

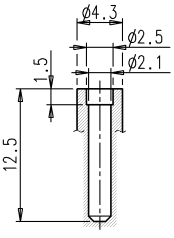


TERMINAL



t=0.8

SECTION A

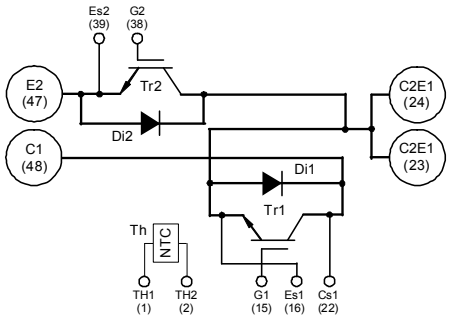


Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

※: Dimensions with a Tolerance of ⊕ ø0.5

INTERNAL CONNECTION



MITSUBISHI ELECTRIC

ABSOLUTE MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/FWDi

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	±20	V
I_C	Collector current	DC, T_C=91 °C (Note.2, 4)	150	A
I_{CRM}		Pulse, Repetitive (Note.3)	300	
P_{tot}	Total power dissipation	T_C=25 °C (Note.2, 4)	960	W
I_E (Note.1)	Emitter current	T_C=25 °C (Note.2, 4)	150	A
I_{ERM} (Note.1)		Pulse, Repetitive (Note.3)	300	

MODULE

Symbol	Item	Conditions	Rating	Unit
T_{jmax}	Maximum junction temperature	-	150	°C
T_{Cmax}	Maximum case temperature	(Note.2)	125	
T_{jop}	Operating junction temperature	-	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V

ELECTRICAL CHARACTERISTICS (T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/FWDi

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	µA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=15 mA, V_{CE}=10 V		6	7	8	V
V_{CEsat} (Terminal)	Collector-emitter saturation voltage	I_C=150 A (Note.5), V_{GE}=15 V	T_j=25 °C	-	2.0	2.6	V
			T_j=125 °C	-	2.2	-	
V_{CEsat} (Chip)	Collector-emitter saturation voltage	I_C=150 A, V_{GE}=15 V (Note.5)		-	1.9	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	23	nF
C_{oes}	Output capacitance			-	-	2.0	
C_{res}	Reverse transfer capacitance			-	-	0.45	
Q_G	Gate charge	V_{CC}=600 V, I_C=150 A, V_{GE}=15 V		-	675	-	nC
$t_{d(on)}$	Turn-on delay time	V_{CC}=600 V, I_C=150 A, V_{GE}=±15 V, R_G=2.2 Ω, Inductive load		-	-	130	ns
t_r	Rise time			-	-	100	
$t_{d(off)}$	Turn-off delay time			-	-	450	
t_f	Fall time			-	-	600	
V_{EC} (Note.1) (Terminal)	Emitter-collector voltage	I_E=150 A (Note.5), G-E short-circuited	T_j=25 °C	-	2.6	3.4	V
			T_j=125 °C	-	2.16	-	
V_{EC} (Note.1) (Chip)	Emitter-collector voltage	I_E=150 A, G-E short-circuited (Note.5)		-	2.5	-	V
t_{rr} (Note.1)	Reverse recovery time	V_{CC}=600 V, I_E=150 A, V_{GE}=±15 V, R_G=2.2 Ω, Inductive load		-	-	150	ns
Q_{rr} (Note.1)	Reverse recovery charge			-	6.0	-	µC
E_{on}	Turn-on switching energy per pulse	V_{CC}=600 V, I_C=I_E=150 A, V_{GE}=±15 V, R_G=2.2 Ω, T_j=125 °C, Inductive load		-	7.0	-	mJ
E_{off}	Turn-off switching energy per pulse			-	15	-	
E_{rr} (Note.1)	Reverse recovery energy per pulse			-	15	-	mJ
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, T_C=25 °C (Note.2)		-	1.6	-	mΩ
r_g	Internal gate resistance	Per switch, T_C=25 °C (Note.2)		-	0	-	Ω

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	T_C=25 °C (Note.2)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	T_C=100 °C, R_{100}=493 Ω	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note.6)	-	3375	-	K
P_{25}	Power dissipation	T_C=25 °C (Note.2)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance (Note.2)	Junction to case, per Inverter IGBT	-	-	0.13	K/W
$R_{th(j-c)D}$		Junction to case, per Inverter FWDi	-	-	0.23	K/W
$R_{th(c-s)}$	Contact thermal resistance (Note.2)	Case to heat sink, per 1 module, Thermal grease applied (Note.7)	-	15	-	K/kW

MECHANICAL CHARACTERISTICS

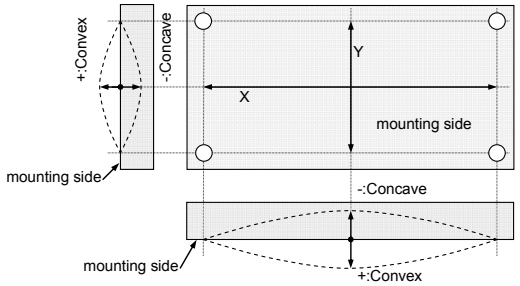
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M_s		Mounting to heat sink M 5 screw	2.5	3.0	3.5	
d_s	Creepage distance	Terminal to terminal	11.55	-	-	mm
		Terminal to base plate	12.32	-	-	
d_a	Clearance	Terminal to terminal	10.00	-	-	mm
		Terminal to base plate	10.85	-	-	
m	Weight	-	-	330	-	g
e_c	Flatness of base plate	On the centerline X, Y (Note.8)	±0	-	+100	μm

Note.1: Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).
Note.2: Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
The heat sink thermal resistance should measure just under the chips.
Note.3: Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
Note.4: Junction temperature (T_j) should not increase beyond T_{jmax} rating.
Note.5: Pulse width and repetition rate should be such as to cause negligible temperature rise.
Refer to the figure of test circuit.

Note.6: $B_{(25/50)} = \ln(\frac{R_{25}}{R_{50}})/(\frac{1}{T_{25}} - \frac{1}{T_{50}})$

R_{25}: resistance at absolute temperature T_{25} [K]; T_{25}=25 [°C]+273.15=298.15 [K]
R_{50}: resistance at absolute temperature T_{50} [K]; T_{50}=50 [°C]+273.15=323.15 [K]

Note.7: Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).
Note.8: Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



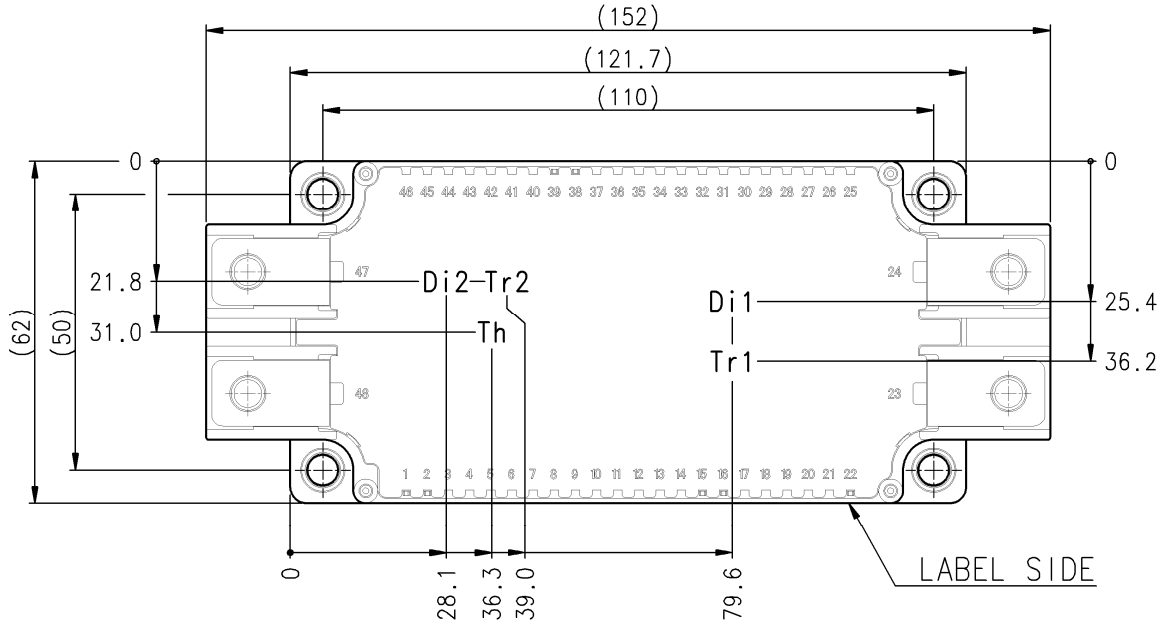
Note.9: JAPAN Electronics and Information Technology Industries Association (JEITA) standard, "ED-4701/300: Environmental and endurance test methods for semiconductor devices (Stress test I)".

RECOMMENDED OPERATING CONDITIONS (T_a=25 °C)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2	-	600	800	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	2.0	-	21	Ω

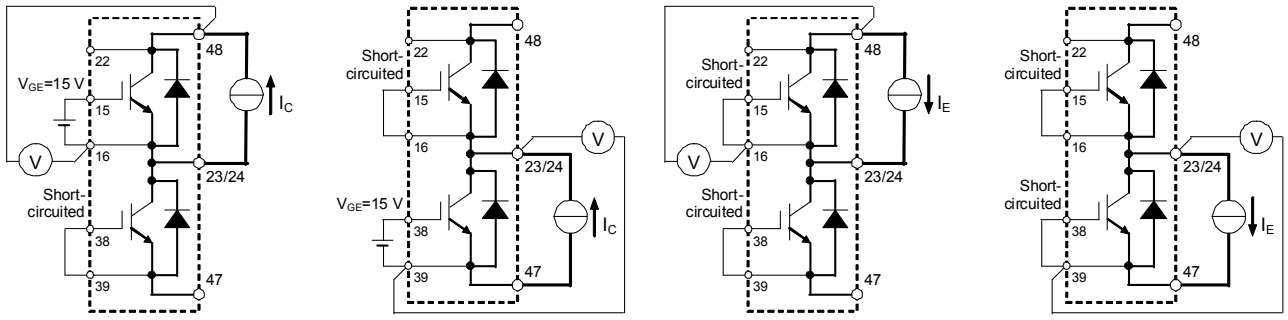
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ±1 mm



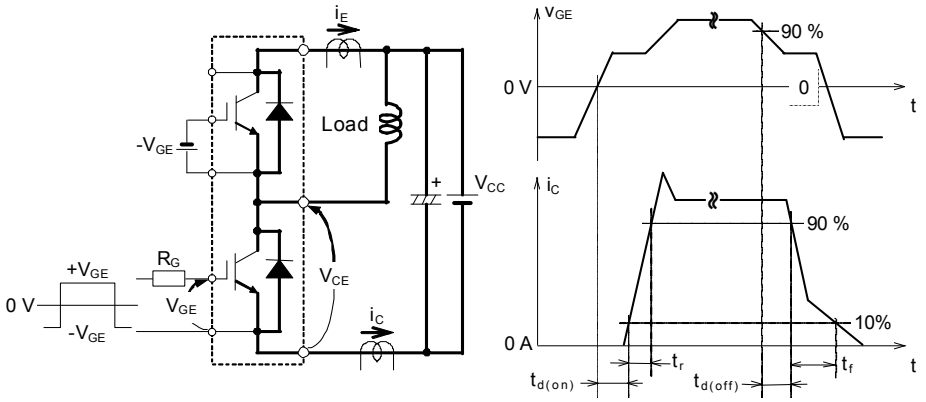
Tr1/Tr2: IGBT, Di1/Di2: FWDi, Th: NTC thermistor. Each mark points the center position of each chip.

TEST CIRCUIT AND WAVEFORMS

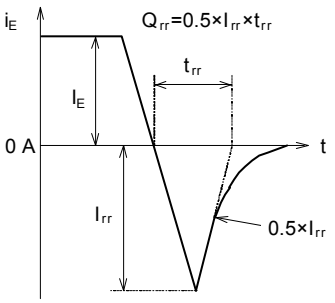


Tr1 Tr2 Di1 Di2

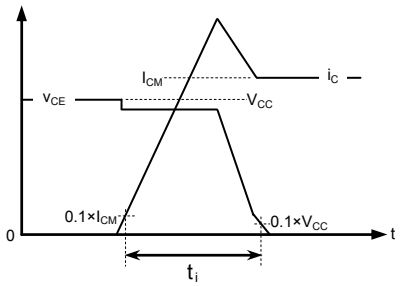
V_{CEsat} test circuit V_{EC} test circuit



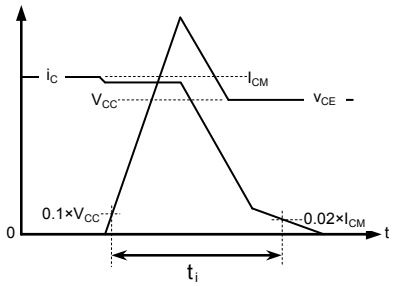
Switching characteristics test circuit and waveforms



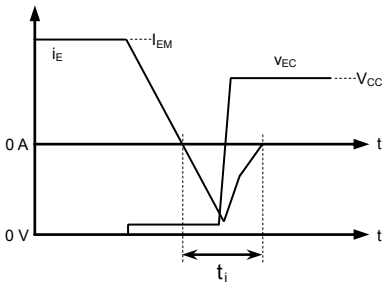
t_{rr}, Q_{rr} test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy



FWDi Reverse recovery energy

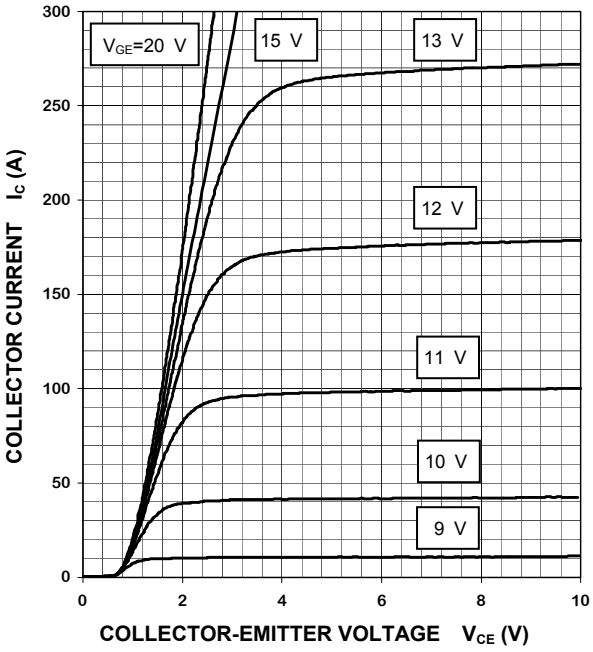
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

PERFORMANCE CURVES

INVERTER PART

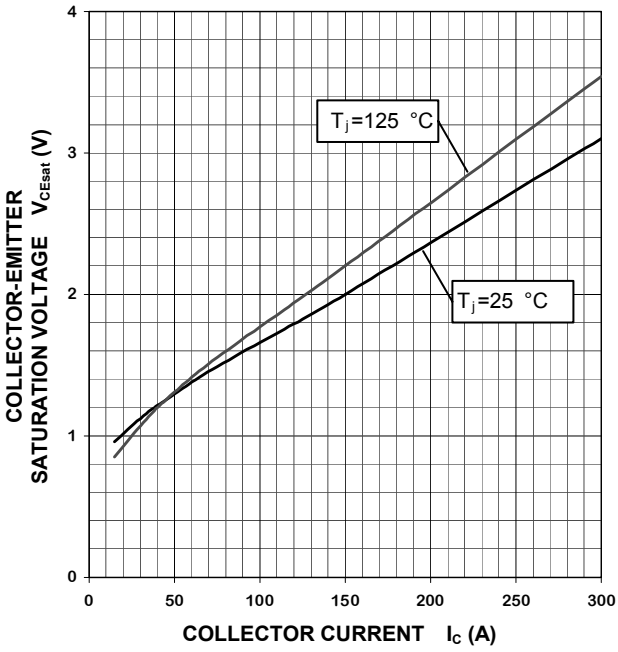
OUTPUT CHARACTERISTICS (TYPICAL)

T_j=25 °C



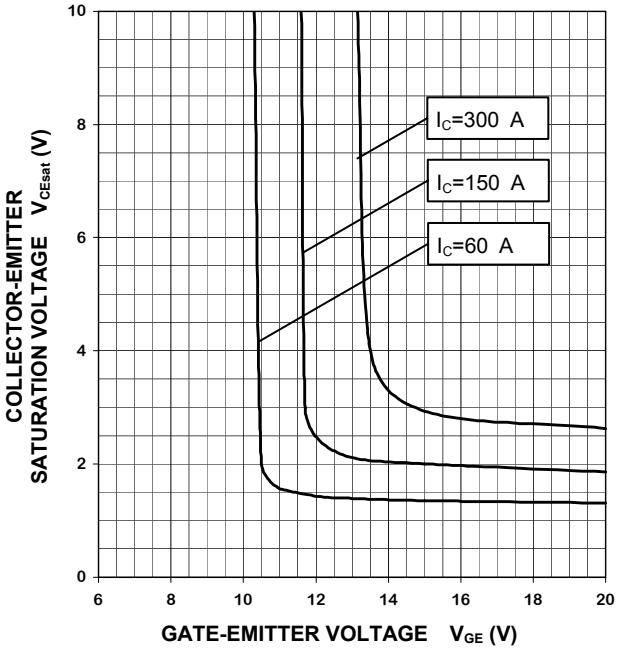
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

V_{GE}=15 V



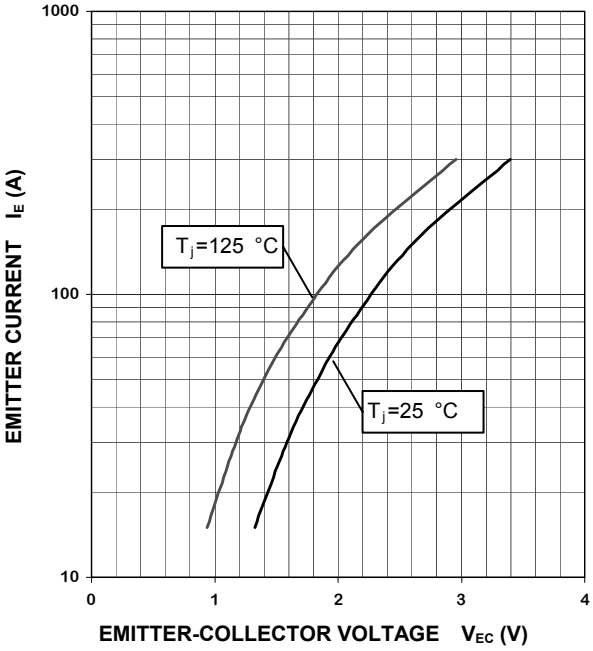
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

T_j=25 °C

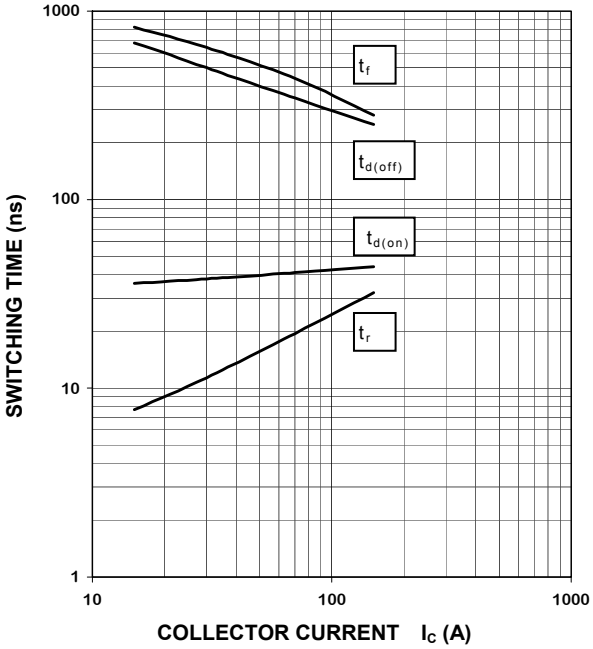


FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)

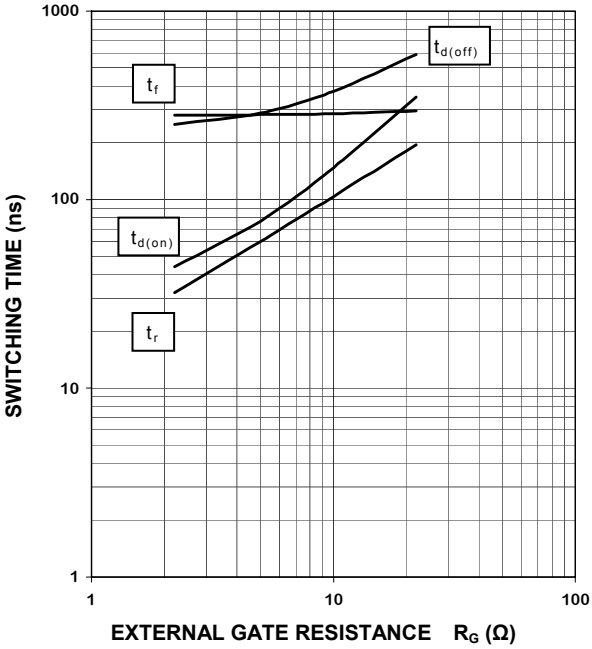
G-E short-circuited



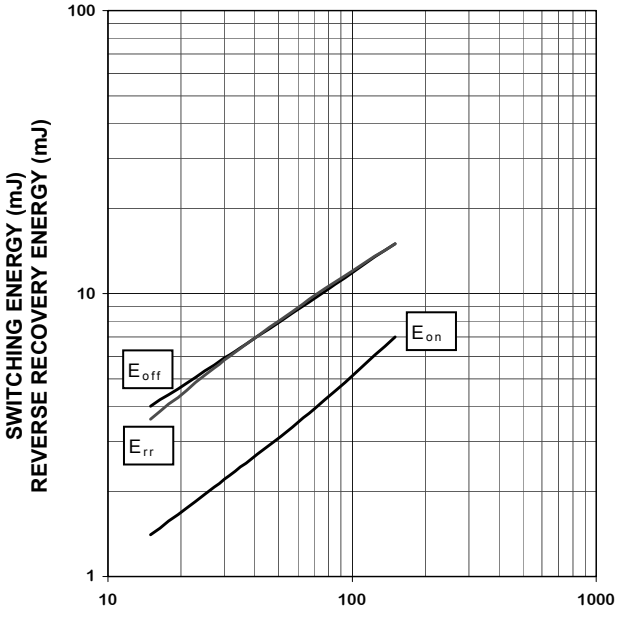
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)
V_{CC}=600 V, V_{GE}=±15 V, R_G=2.2 Ω,
INDUCTIVE LOAD, T_j=125 °C



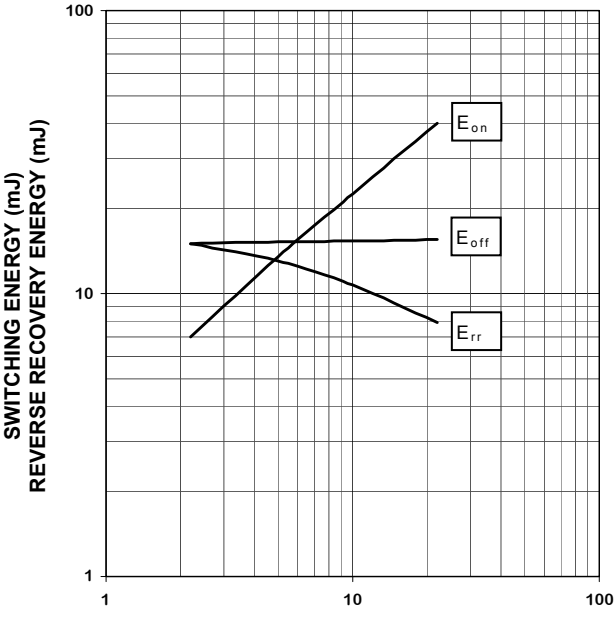
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)
V_{CC}=600 V, I_C=150 A, V_{GE}=±15 V,
INDUCTIVE LOAD, T_j=125 °C



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)
V_{CC}=600 V, V_{GE}=±15 V, R_G=2.2 Ω,
INDUCTIVE LOAD, PER PULSE, T_j=125 °C

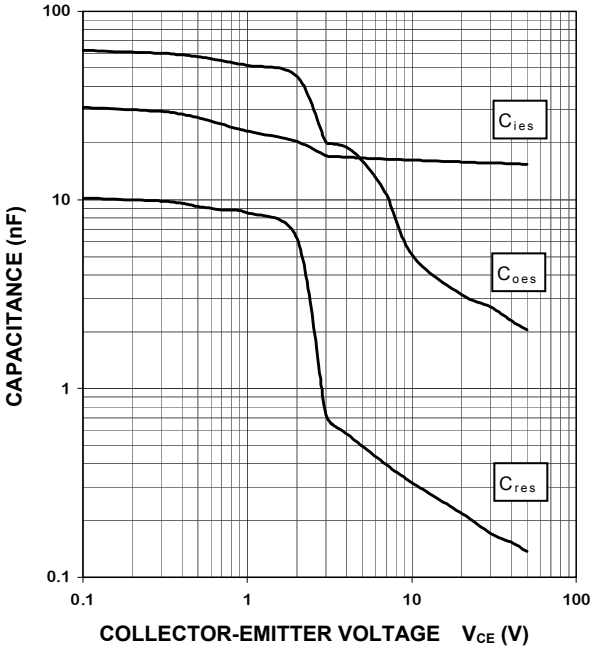


HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)
V_{CC}=600 V, I_C/I_E=150 A, V_{GE}=±15 V,
INDUCTIVE LOAD, PER PULSE, T_j=125 °C



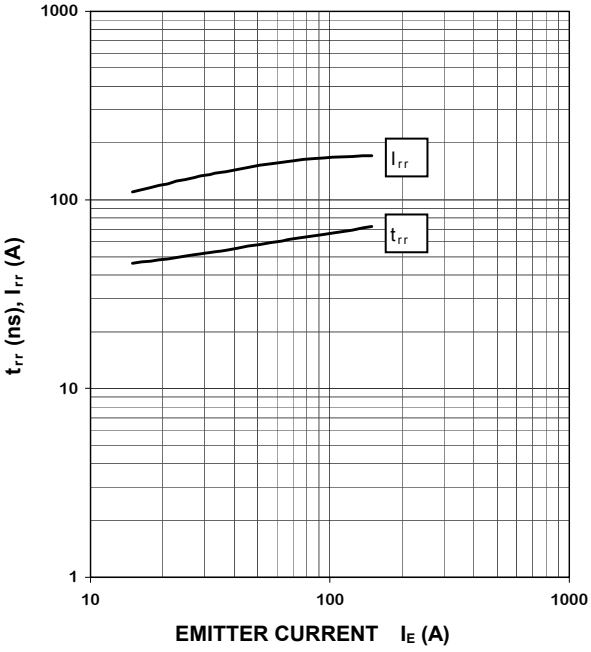
CAPACITANCE CHARACTERISTICS (TYPICAL)

G-E short-circuited, T_j=25 °C



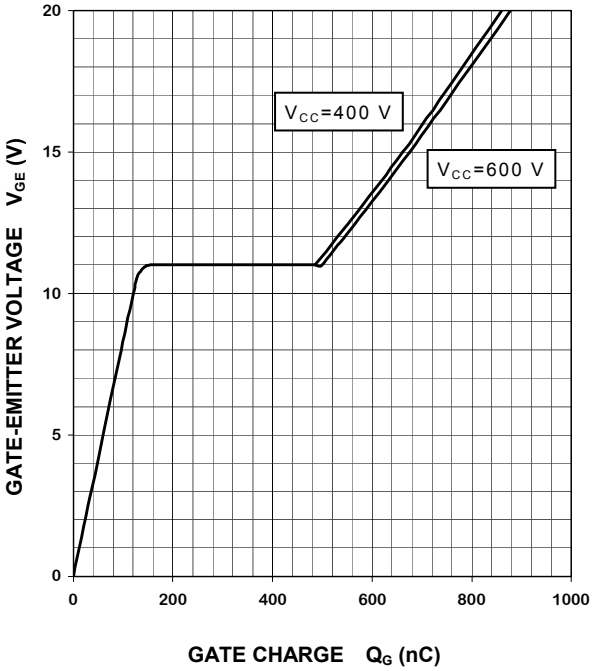
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

V_{CC}=600 V, V_{GE}=±15 V, R_G=2.2 Ω, INDUCTIVE LOAD, T_j=25 °C



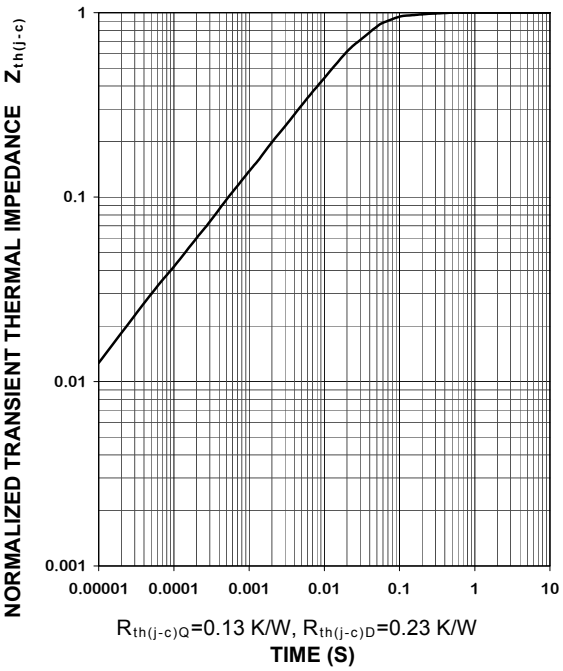
GATE CHARGE CHARACTERISTICS (TYPICAL)

I_C=150 A, T_j=25 °C



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

Single pulse, T_C=25°C



$R_{th(j-c)Q}$=0.13 K/W, $R_{th(j-c)D}$=0.23 K/W

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